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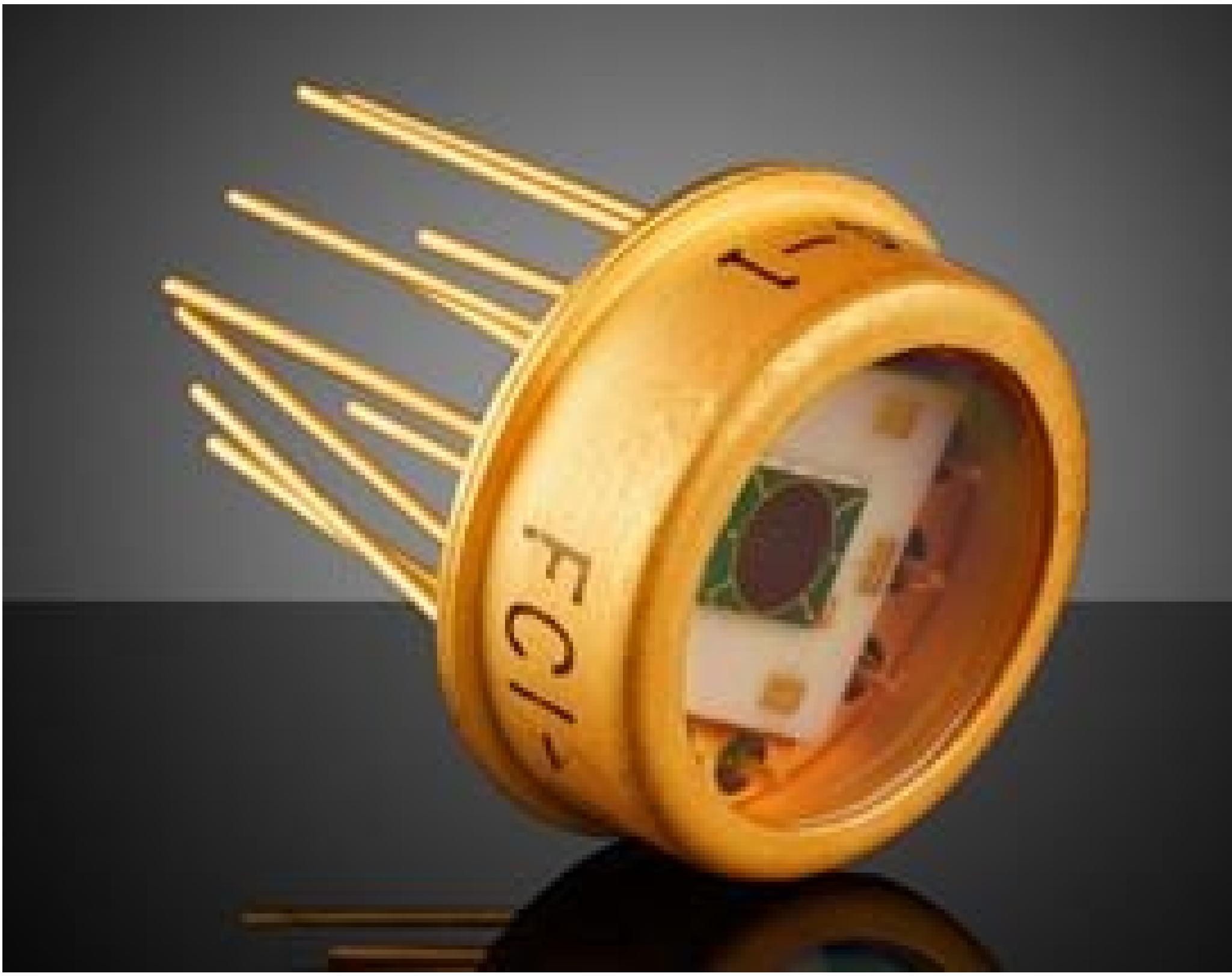
3mm Dia., Four-Element Segmented InGaAs Photodiode



#17-078, 3mm Dia., Four-Element Segmented InGaAs Photodiode

Stock **#17-078** **3 In Stock**

- 1 +

A$984.00

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Volume Pricing	
Qty 1-4	**A$984.00** each
Qty 5-9	**A$872.00** each
Qty 10-24	**A$811.20** each
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Product Downloads

General

Rise/ Fall Time @ V_R=5V (ns):
24 (typical)

Physical & Mechanical Properties

Size of Active Area (mm):
3 Dia.

Element Gap (mm):
0.045

Electrical

Responsivity @ 1310nm (A/W):
0.85 minimum / 0.9 typical

Responsivity @ 1550nm (A/W):
0.9 minimum / 0.95 typical

Capacitance @ V_R=5V (pF):
225

Noise Equivalent Power NEP (W/ $Hz^{1/2}$):
2.50×10^{-14} @ 1550nm

Maximum Reverse Voltage (V):
10

Dark Current @ V_R=5V (nA):
Maximum: 100 Typical: 2.0

Hardware & Interface Connectivity

Connector:
TO-8

Environmental & Durability Factors

Operating Temperature (°C):
-40 to +75

Storage Temperature (°C):
-55 to +125

Regulatory Compliance

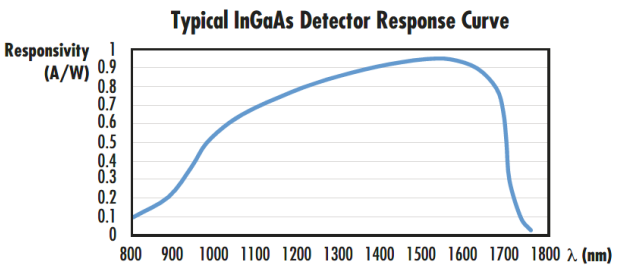
Certificate of Conformance:
View

Product Details

- Four Individual Active Area Elements
- High Response Uniformity and Low Crosstalk
- Ideal for Position Detection and Beam Alignment
- **Segmented Silicon Photodiodes** and **InGaAs Photodiodes** Also Available

Segmented InGaAs Photodiodes feature large active areas divided into four individual elements. The four elements of these photodiodes have high response uniformity and low crosstalk, enabling their use in accurate nulling or centering applications. These photodiodes are stable over time and temperature, providing responsivity from 900 - 1700nm with excellent responsivity between 1100 - 1620nm. Segmented InGaAs Photodiodes are ideal for position detection, beam alignment, and beam profiling applications in the near-infrared spectrum. Each photodiode is packaged in an isolated TO-5 or TO-8 can with an antireflection coated window to increase throughput.

Technical Information



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